

SILICON DARLINGTON POWER TRANSISTORS BDT62; 62A BDT62B; 62C

P-N-P epitaxial base transistors in monolithic Darlington circuit for audio output stages and general amplifier and switching applications. TO-220 plastic envelope. N-P-N complements are BDT63, BDT63A, BDT63B and BDT63C.

QUICK REFERENCE DATA

			BDT62	A	B	C
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	60	80	100	120 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	60	80	100	120 V
Collector current (d.c.)	$-I_C$	max.			10	A
Collector current (peak value) $\tau_p = 0,3 \text{ ms}; \delta = 10\%$	$-I_{CM}$	max.			15	A
Total power dissipation up to $T_{mb} = 25^\circ\text{C}$	P_{tot}	max.			90	W
Junction temperature	T_j	max.			150	$^\circ\text{C}$
D.C. current gain $-I_C = 3 \text{ A}; -V_{CE} = 3 \text{ V}$	h_{FE}	>			1000	

MECHANICAL DATA

Fig. 1 TO-220AB.

Collector connected to mounting base.

